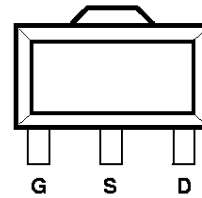


- **Wide Operating Frequency Range up to 1000 MHz**
- **High Output Power:**
Typical Value of 32.5 dBm at 4.8 V and 900 MHz
Typical Value of 29 dBm at 3.6 V and 900 MHz
- **High Gain:**
Typical Value of 9.5 dB at 4.8 V, and 900 MHz at 32.5-dBm Output Power
- **High Power-Added Efficiency (PAE):**
Typical Value of 50% at 32.5-dBm Output Power
- **Low Cost**
- **Extremely Rugged:**
Sustains 20:1 Load Mismatch
- **Suitable for Various Wireless Applications**
- **Low Leakage <1 μ A**
- **SOT-89 Plastic Power Package**

PK PACKAGE
(TOP VIEW)



description

The TRF7003 power amplifier is a silicon, metal-oxide semiconductor, field-effect transistor (MOSFET) manufactured using the Texas Instruments RFMOS™ process. It is housed in a SOT-89 (PK) plastic power package. The TRF7003 is intended for global systems for mobile communications (GSM) power amplifier applications. The TRF7003 is a rugged, low-cost device that operates from a single-polarity positive power supply and has low leakage current. Typical power output at 900 MHz is 32.5 dBm, with an associated power gain of 9.5 dB and 50-percent power-added efficiency (PAE).



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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